Title (en)

METHOD FOR PRODUCING DEEP TRENCH STRUCTURES

Title (de)

VERFAHREN ZUR HERSTELLUNG VON DEEP-TRENCH-STRUKTUREN

Title (fr)

PROCEDE DE PRODUCTION DE STRUCTURES A TRANCHEE PROFONDE

Publication

EP 1825506 A1 20070829 (DE)

Application

EP 05819407 A 20051213

Priority

- EP 2005013359 W 20051213
- DE 102004060821 A 20041217

Abstract (en)

[origin: WO2006066755A1] The invention relates to a method for producing deep trench structures in an STI structure of a semiconductor body, comprising the following steps: introducing STI recesses into the semiconductor body and filling them with a first filling material; subjecting a first surface of a semiconductor structure to a CMP process, thereby leveling the filling material applied and producing the STI structure; structuring the leveled STI structure so produced; etching at least one deep trench in the area of the STI structure using the structured, leveled STI structure as the hard mask, thereby producing the deep trench structures.

IPC 8 full level

H01L 21/762 (2006.01)

CPC (source: EP US)

H01L 21/76224 (2013.01 - EP US)

Citation (search report)

See references of WO 2006066755A1

Designated contracting state (EPC)

DE FR

DOCDB simple family (publication)

DE 102004060821 A1 20060629; **DE 102004060821 B4 20110428**; EP 1825506 A1 20070829; US 2007264792 A1 20071115; US 7851326 B2 20101214; WO 2006066755 A1 20060629

DOCDB simple family (application)

DE 102004060821 A 20041217; EP 05819407 A 20051213; EP 2005013359 W 20051213; US 81238607 A 20070618